

Fast Diffusion Mechanism of Silicon Tri-interstitial Defects

Yaojun A. Du,¹ Stephen A. Barr,² Kaden R. A. Hazzard,³
Thomas J. Lenosky,¹ Richard G. Hennig,¹ and John W. Wilkins¹

¹*Department of Physics, Ohio State University, Columbus, OH, USA*

²*Department of Materials Science and Engineering,*

University of Illinois at Urbana-Champaign, Urbana, Illinois, USA

³*Department of Physics, Cornell University, Ithaca, NY, USA*

(Dated: February 2, 2008)

Molecular dynamics combined with the nudged elastic band method reveals the microscopic self-diffusion process of compact silicon tri-interstitials. Tight-binding molecular dynamics paired with *ab initio* density functional calculations speed the identification of diffusion mechanisms. The diffusion pathway can be visualized as a five defect-atom object both translating and rotating in a screw-like motion along $\langle 111 \rangle$ directions. Density functional theory yields a diffusion constant of $4 \times 10^{-5} \exp(-0.49 \text{ eV}/k_B T) \text{ cm}^2/\text{s}$. The low-diffusion barrier of the compact tri-interstitial may be important in the growth of ion-implantation-induced extended interstitial defects.

PACS numbers: 61.72.Ji, 66.30.Lw, 71.15.Mb, 71.15.Pd

Keywords: silicon; self-diffusion; interstitial defects; *ab initio*; molecular dynamics

Following high-energy ion implantation, strongly supersaturated silicon self-interstitials can agglomerate to form macroscopic planar interstitial structures, $\{311\}$ defects [1]. High-temperature annealing is necessary to remove lattice damage following ion implantation. However during the annealing process the $\{311\}$ defects comprise a large reservoir of interstitials [2, 3, 4], which are released upon annealing and hence drive boron transient enhanced diffusion [5, 6, 7], an undesirable process which causes spatial broadening of boron concentration profiles. On the other hand, following low-energy implantation, significant boron TED is still observed, even though no visible $\{311\}$ defects are developed [7].

It is crucial to understand the diffusion of various point defects in order to have a quantitative understanding of boron TED. Measurements of the diffusion rate of defects in silicon have been reported in experiments [8, 9, 10, 11, 12, 13, 14]. Current experimental techniques cannot cleanly resolve the diffusion rates of more complex defect species, and due to the atomic-scale size of point defects, defect diffusion pathways cannot be resolved at all [15]. Thus, numerical simulations provide a unique way to study the technologically-important dynamics of point defects in crystalline silicon.

Previously, such simulations have studied numerous defect species using both classical and quantum Hamiltonians [16, 17, 18, 19, 20]. Using nudged elastic band methods (NEB) [21] within density functional theory (DFT) code, Lopez *et al.* compute an activation energy of 0.28 eV for a neutral single interstitial diffusing along the X - T - X path [22]. Kim *et al.* estimates the self-diffusion barrier of a particular di-interstitial performing a reorientation to be 0.5 eV [17]. Recent DFT-NEB calculations done in our group confirm this pathway but give a somewhat lower barrier of 0.3 eV [38].

Cogoni *et al.* [23] use temperature-accelerated molecular-dynamics [24] with the Kwon *et al.* [25] tight-binding (TB) potential to systematically study the dif-

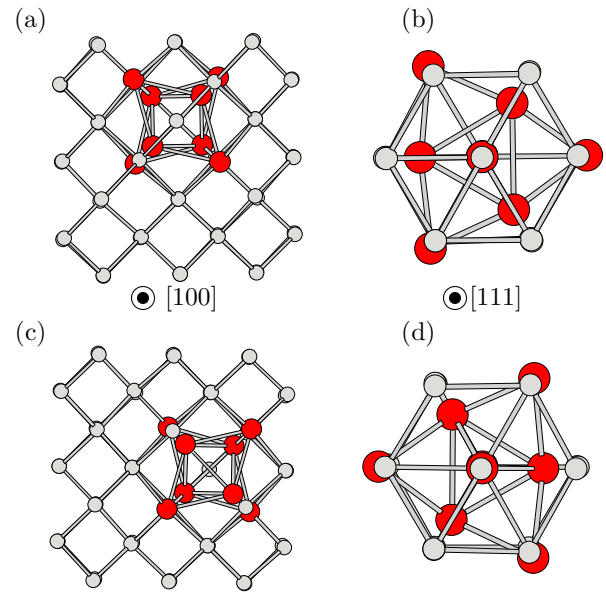


FIG. 1: Diffusion of I_3^b to the neighboring site along the $\langle 111 \rangle$ direction. The initial configurations viewed from $[110]$ and $[111]$ are shown in (a) and (b), respectively. The final configurations viewed from $[110]$ and $[111]$ are shown in (c) and (d), respectively. Defect atoms are shaded. All of the above structures are relaxed using density functional theory.

fusion of low-lying single-, di- and tri-interstitials. In particular they find all are fast diffusers with diffusion barriers of 0.94, 0.89 and 1.71 eV, respectively. We extend that work both with a more accurate tight-binding potential and with density-functional theory to further refine the diffusion pathway and the diffusion constant. Here we concentrate on the tri-interstitial finding an activation energy of 0.4-0.5 eV in DFT (and 0.6 eV in TB).

Which tri-interstitial to study? In a previous work from our research group [26], the three lowest-energy

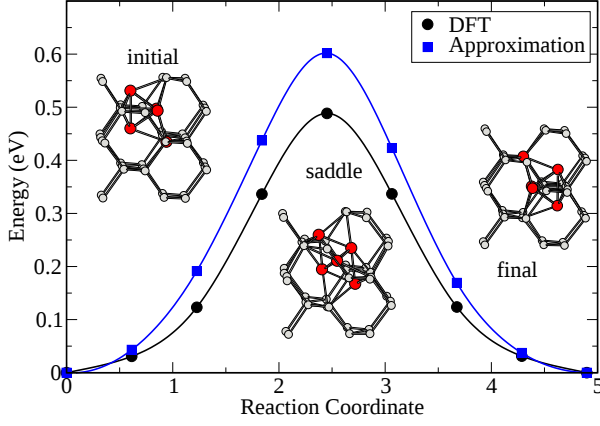


FIG. 2: Transition paths of I_3^b in DFT-GGA and the approximation of collective motion of five atoms within DFT-GGA. Five atoms are highlighted in gray for the initial state, saddle point and final state in the insets, respectively.

tri-interstitial geometries, denoted I_3^a , I_3^b , and I_3^c , were identified by analysis of tight-binding molecular dynamics (MD) simulations followed by density functional relaxations. The TB calculations use the Lenosky *et al.* [27] potential. I_3^a is the ground state and I_3^b and I_3^c are excited states [39]; the density functional energies for the three defects in 216+3 atom supercells were 2.24 eV/atom, 2.37 eV/atom, and 2.47 eV/atom respectively. The tight-binding MD simulations show only I_3^b is a rapid diffuser, while I_3^a and I_3^c can be formed by interconversion of I_3^b , but are themselves immobile within the 5 ns time scale of the simulations [26]. Hence, we focus on elucidating the microscopic diffusion process of the compact tri-interstitial I_3^b . I_3^b has a compact defect geometry in which a perfect tetrahedron of four atoms replaces a single atom in the silicon lattice, with the faces oriented along the four symmetry related $\langle 111 \rangle$ directions.

Tight-binding molecular dynamics determines an initial I_3^b diffusion path. Density-functional theory uses the nudged-elastic-band method to refine the diffusion path and determines the accurate diffusion barrier. The self-diffusion of I_3^b can be visualized in terms of the atoms most distorted during the process. In particular a five-atom object translates while rotating to avoid adjacent atoms. NEB finds four equivalent paths along $\langle 111 \rangle$ with a diffusion constant of $D = 4 \times 10^{-5} \exp(-0.49 \text{ eV}/k_B T) \text{ cm}^2/\text{s}$.

Minimum energy path / nudged elastic band. Figure 1 shows two I_3^b defects in neighboring sites that correspond to initial and final configurations along the diffusion path, the $\langle 111 \rangle$ direction. We obtain the initial pathway from analysis of molecular dynamics trajectories [26]. The climbing-image NEB (CI-NEB) method [28] refines an accurate pathway and finds the diffusion barrier between these two I_3^b minima. The CI-NEB scheme guarantees that the image with the highest energy converges to the saddle point. All NEB calculations are performed with

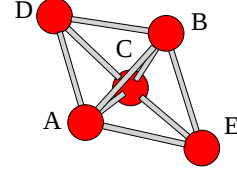


FIG. 3: Five most displaced atoms during the diffusion. These five atoms move collectively. Atom D and E define an axis of rotation ($\langle 111 \rangle$), around which atom A, B and C are rotating.

the VASP density functional code [29, 30] employing the Perdew-Wang GGA functional [31], and ultra-soft Vanderbilt-type pseudopotentials [32] as provided by G. Kresse and J. Hafner [33]. An initial relaxation of the two end points initiates a full relaxation of seven images along the path, keeping the volume of the cell fixed. Energy and atomic position convergence of 3 meV and 0.005 Å, respectively, is confirmed for 64+3 atom supercell by comparing the results for a 250 eV energy cutoff and a $3 \times 3 \times 3$ k-point mesh with a 300 eV cutoff and a $4 \times 4 \times 4$ mesh. The seven images are initialized by linear interpolation between the two relaxed end points. Each of the images is relaxed until the atomic and spring forces are less than 10 meV/Å.

Figure 2 shows the diffusion path with an activation energy of 0.49 eV. Harmonic transition state theory [34] calculates the defect jump rate Γ from the phonon frequencies at the minimum $\nu_i^{\min}$ and at the saddle point ν_i^{sad} and the activation energy ΔE

$$\Gamma = \Gamma_0 e^{-\Delta E/k_B T}, \quad (1)$$

where the prefactor Γ_0 is given by:

$$\Gamma_0 = \prod_i^{3N-3} \nu_i^{\min} / \prod_i^{3N-4} \nu_i^{\text{sad}}. \quad (2)$$

The dynamical matrix method within *ab initio* GGA density functional theory determines the phonon frequencies. Each atom is displaced in the $\hat{x}$, $\hat{y}$, $\hat{z}$ direction by 0.03 Å and the calculated forces are used to construct the Hessian matrix for the system, which is diagonalized to find the phonon frequencies. This yields a jump rate $\Gamma = 0.2 \text{ THz} \exp(-0.49/k_B T)$. Calculations for a larger cell of 216+3 atoms provide a diffusion barrier of 0.43 eV estimating a finite size error of about 0.1 eV.

Collective motion of atoms. In the diffusion event, the five most-displaced atoms move collectively, with a screw-like motion. The insets in Figure 2, showing the atomic configurations for initial, saddle and final states, indicate significant displacement of the five solid-colored atoms. All other atoms relax only slightly during the diffusion with a maximum displacement of 0.18 Å.

In order to illustrate the screw-like collective motion, we highlight the five highly-displaced atoms in Figure 3.

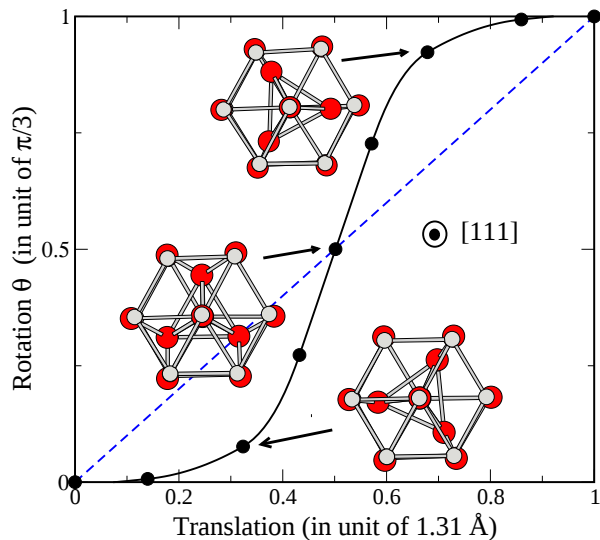


FIG. 4: Transition path with seven images projected onto two-dimensional reduced coordinates. The inset shows images 3, 5 (saddle point), and 7 along the transition path.

TABLE I: The translation and rotation of five atoms along the $[111]$ direction with respect to the initial state for all seven images in Fig 4.

image	Translation (Å)	Rotation (degree)
1	0.18	0.4
2	0.42	4.6
3	0.57	16.4
4	0.66	30.0
5	0.75	43.6
6	0.89	55.4
7	1.13	59.6

Atom A, B, and C are located in a (111) plane, forming an equilateral triangle, and translate along and rotate about the $[111]$ axis defined by atom D and E. Meanwhile, atoms D and E translate along the same $[111]$ direction. Atoms D, A and B form an equilateral triangle, whose normal vector indicates another diffusion direction, and all five atoms form a double-tetrahedron. The bond between A and B is 2.49 Å at the minimum, 6% longer than the perfect silicon-silicon bulk bond distance. During the diffusion event this bond length varies by less than 4.5%. During defect migration the double-tetrahedron translates 1.31 Å and rotates 60 degrees as shown in Figure 1 and the insets of Figure 2. Table I lists the values for the translation and rotation of the seven relaxed NEB images.

The diffusion event is approximated by a uniform translation and rotation of a fixed double-tetrahedron. For instance, rotating the double-tetrahedron of the initial configuration (image 1) by 16.4 degrees, and translating it by 0.57 Å while keeping its geometry fixed and relaxing the other atoms provides an approximation to image 3. Applying this procedure to each of the im-

TABLE II: Formation and activation energy of the neutral single-interstitial diffusing along the $X-T-X$ path, and of the neutral ground state di-interstitial and compact tri-interstitial during self-diffusion. The formation energies are calculated in a $216 + n$ atom supercell and the activation energies are calculated using NEB with a $64 + n$ atom supercell. Details of the diffusion paths of single- and di-interstitials will be published elsewhere [38].

	Formation energy /atom (eV)	Activation energy (eV)
I_1	3.810	0.29, 0.28 ^a
I_2	2.827	0.30
I_3^b	2.368	0.49

^aNEB result from Ref. [22] is calculated using $216 + 1$ atom supercell.

ages along the diffusion path, we obtain the approximate diffusion path in Figure 2. The approximate activation energy is 0.6 eV, only 20% higher than the fully relaxed value.

Figure 4 shows the translation and rotation of the double-tetrahedron during the diffusion. Translation occurs before the structure rotates. The double-tetrahedron is displaced half way and rotated 30 degrees at the saddle point. The insets show images 3, 5 (saddle point) and 7 viewed from the $[111]$ direction and illustrate that three-fold symmetry persists during the diffusion.

Diffusion rate. The defect I_3^b can move to four neighboring sites along the four symmetry-equivalent $\langle 111 \rangle$ directions. The diffusion constant for this random walk is $D = 2 \frac{4}{6} a^2 \Gamma$ (derivation is given in Ref. [35]), where the jump rate Γ is defined by Eq. 1 and the displacement during the diffusion event is $a = 1.31 \text{ Å}$. The factor two takes into account the fact that the defect can rotate either in clockwise or counter-clockwise direction during the diffusion. The resulting diffusion constant is $D = 4 \times 10^{-5} \exp(-0.49 \text{ eV}/k_B T) \text{ cm}^2/\text{s}$.

Discussion. Table II summarizes the *ab initio* density functional theory results for formation and activation energy of I_1 , I_2 , and compact I_3 defects. The theoretical values of 0.28 to 0.49 eV are considerably lower than the experimental results from metal-diffusion experiments which find activation energies, believed to be for single interstitials, typically ranging from ~ 1.4 to 1.8 eV [36]. However, a recent experiment [14] identifies enhanced diffusion of single interstitials at 150 K, while noting it is inconsistent with results from earlier approaches. This lower temperature would be consistent with the NEB result for the energy barrier of single interstitial diffusion of 0.3 eV.

Our pathway for I_3 diffusion is the same as that found by Cogoni *et al.* [23] in the $64 + 3$ atom supercell. On the other hand, our DFT barriers for I_1 , I_2 , and I_3 of 0.3, 0.3 and 0.4-0.5 eV are much smaller than the tight-binding results by Cogoni *et al.* [23] of 0.9, 0.9 and 1.7 eV. We also perform the NEB calculation to examine the diffusion path of the compact tri-interstitial within Kwon's potential [25], and obtain a diffusion barrier of

1.2 eV in contrast to 0.6 eV barrier within Lenosky's TB potential [27]. The Kwon's potential overestimates the phonon frequencies [27], which makes a local minimum steeper. This suggests that Kwon's potential will consequently overestimate the barrier for the interstitial diffusion, which is characterized by the small displacements of several atoms deviating from the equilibrium sites.

We perform density of states (DOS) calculations for the interstitial defect along the diffusion path within a $216 + 3$ atom supercell. The DOS is calculated for the minimum, the saddle point and an intermediate structure. The DOS shows a band gap of 0.71-0.74 eV for all three configurations along the diffusion pathway. There are no states in the gap. The size of the gap is close to the band gap of pure Si in GGA of 0.72 eV. The lack of gap states indicates that charge transfer may not play a significant role for the diffusion of a compact tri-interstitial.

While the formation energy of I_3 is lower than I_1 on a per-atom basis, it is much higher when considered on a total basis. One implication that can be drawn from this is that under equilibrium conditions, I_3 is not present in any significant quantity, but under conditions which

inject excess interstitials [5], such as ion implantation, it may be present in significant amounts. Our results have possible relevance for modeling transient enhanced diffusion which follows ion implantation [37].

Conclusions. We have elucidated the pathway for the diffusion of the compact tri-interstitial, I_3^b , the only fast-diffusing tri-interstitial species in crystalline silicon. During the self-diffusion event, five atoms move collectively in a screw-like motion along one of four symmetry-related $\langle 111 \rangle$ directions. Our DFT result shows a low activation energy of 0.49 eV and a diffusion constant of $4 \times 10^{-5} \exp(-0.49 \text{ eV}/k_B T) \text{ cm}^2/\text{s}$. Under conditions such as ion implantation that creates excess interstitials and hence favor cluster formation, I_3^b diffusion may be an important process due to the low activation energy.

Acknowledgments. The work was supported in part by DOE-Basic Energy Sciences, Division of Materials Sciences (DE-FG02-99ER45795). Computing resources were provided by the Ohio Supercomputing Center. We also wish to acknowledge helpful conversations with Jeongnim Kim.

-
- [1] I. G. Salisbury and M. H. Loretto, *Philos. Mag. A* **39**, 317 (1979).
 - [2] S. Takeda, *Jpn. J. Appl. Phys.* **30**, L639 (1991).
 - [3] M. Kohyama and S. Takeda, *Phys. Rev. B* **46**, 12305 (1992).
 - [4] J. Kim, J. W. Wilkins, F. S. Khan, A. Canning, *Phys. Rev. B* **55**, 16186 (1997).
 - [5] D. J. Eaglesham, P. A. Stolk, H.-J. Grossmann and K. M. Poate, *Appl. Phys. Lett.* **65**, 2305 (1994).
 - [6] A. Stolk *et al.*, *J. Appl. Phys.* **81**, 6031 (1997).
 - [7] L. H. Zhang, K. S. Jones, P. H. Chi and D. S. Simons, *Appl. Phys. Lett.* **67**, 2025 (1995).
 - [8] T. Y. Tan, and U. Gösele, *Appl. Phys. A* **37**, 1 (1985).
 - [9] H. Bracht, N. A. Stolwijk and H. Mehrer, *Phys. Rev. B* **52**, 16 542 (1995).
 - [10] H. Zimmermann and H. Ryssel, *Appl. Phys. A* **55**, 121 (1992).
 - [11] C. Boit, F. Lau and R. Sittig, *Appl. Phys. A* **50**, 197 (1990).
 - [12] G. B. Bronner and J. D. Plummer, *J. Appl. Phys.* **61**, 5286 (1987).
 - [13] W. Wijaranakula, *J. Appl. Phys.* **67**, 7624 (1990).
 - [14] P. Partyka *et al.*, *Phys. Rev. B* **64**, 235207 (2001).
 - [15] J. L. Benton, S. Libertino, P. Krieho and D. J. Eaglesham, *J. Appl. Phys.* **82**, 120 (1997).
 - [16] Y. Bar-Yam, J. D. Joannopoulos, *Phys. Rev. Lett.* **52**, 1129 (1984).
 - [17] J. Kim *et al.*, *Phys. Rev. Lett.* **83**, 1990 (1999).
 - [18] S. K. Estreicher, M. Gharaibeh, P. A. Fedders and P. Ordejon, *Phys. Rev. Lett.* **86**, 1247 (2001).
 - [19] M. Gharaibeh, S. K. Estreicher, P. A. Fedders, *Physica B* **308-310**, 1 (2001).
 - [20] S. Birner *et al.*, *Solid State Comm.* **120**, 279 (2001).
 - [21] H. Jónsson, G. Mills, and K. W. Jacobsen, in *Classical and Quantum Dynamics in Condensed Phase Simulations*, edited by B. J. Berne, G. Ciccotti, and D. F. Coker (World Scientific, Singapore, 1998), P. 385.
 - [22] G. M. Lopez and V. Fiorentini, *Phys. Rev. B* **69**, 155206 (2004).
 - [23] M. Cogoni, B. P. Uberuaga, A. F. Voter and L. Colombo, *Phys. Rev. B* **71**, 121203(R) (2005).
 - [24] M. R. Sørensen and A. F. Voter, *J. Chem. Phys.* **112**, 9599 (2000).
 - [25] I. Kwon, R. Biswas, C. Z. Wang, K. M. Ho, and C. M. Soukoulis, *Phys. Rev. B* **49**, 7242 (1994).
 - [26] D. A. Richie, J. Kim, S. A. Barr, K. R. A. Hazzard, R. Hennig, and J. W. Wilkins, *Phys. Rev. Lett.* **92**, 045501 (2004).
 - [27] T. J. Lenosky *et al.*, *Phys. Rev. B* **55**, 1528 (1997).
 - [28] G. Henkelman, B. P. Uberuaga and H. Jónsson, *J. Chem. Phys.* **113**, 9901 (2000).
 - [29] G. Kresse and J. Hafner, *Phys. Rev. B* **47**, R558 (1993).
 - [30] G. Kresse and J. Furthmüller *Phys. Rev. B* **54**, 11169 (1996).
 - [31] J. P. Perdew, in *Electronic Structure of Solids '91*, edited by P. Ziesche and H. Eschrig (Akademie Verlag, Berlin: 1991), p. 11.
 - [32] D. Vanderbilt, *Phys. Rev. B* **41**, R7892 (1990).
 - [33] G. Kresse and J. Hafner, *J. Phys.: Cond. Mat.* **6**, 8245 (1994).
 - [34] G. H. Vineyard, *J. Phys. Chem. Solids* **3**, 121 (1957).
 - [35] P. Haasen. *Physical Metallurgy*. Third edition. Cambridge University Press: Cambridge (1996). A. R. Allnatt and A. B. Lidiard. *Atomic transport in solids*. Cambridge University Press: Cambridge (1993).
 - [36] H. Bracht, *Proc. Electrochem. Soc.* **99**, 357 (1999).
 - [37] I. Martin-Bragado *et al.*, *Phys. Rev. B* **68**, 195204 (2003)
 - [38] To be published elsewhere.
 - [39] It should be noted that our notation differs from that of Estreicher *et al.* [18]; our I_3^b geometry corresponds to

their I_3^a .